

BC184, B, C TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 0.35 \text{ W (Tamb=25°C)}$$

Collector current

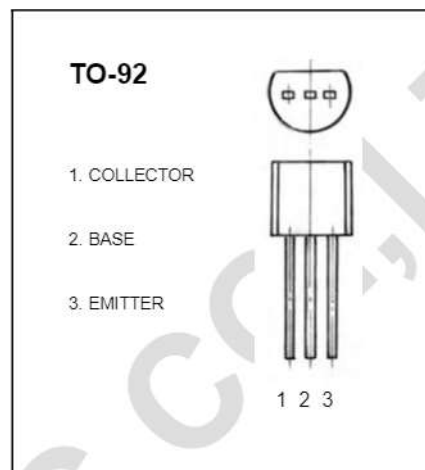
$$I_{CM}: 0.1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 45 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	45		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=2mA, I_B=0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$		15	nA
Collector cut-off current	I_{CEO}	$V_{CE}=30V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$		15	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=2mA$	240 240 450	900 500 900	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=5mA$		0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=5mA$		1.2	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA$ $f=100MHz$	150		MHz